

# Agilent MSA-0470 Cascadable Silicon Bipolar MMIC Amplifier

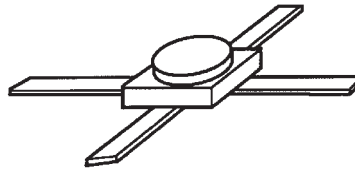
## Data Sheet

### Description

The MSA-0470 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic, high reliability package. This MMIC is designed for use as a general purpose 50  $\Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using Agilent's 10 GHz  $f_T$ , 25 GHz  $f_{MAX}$ , silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

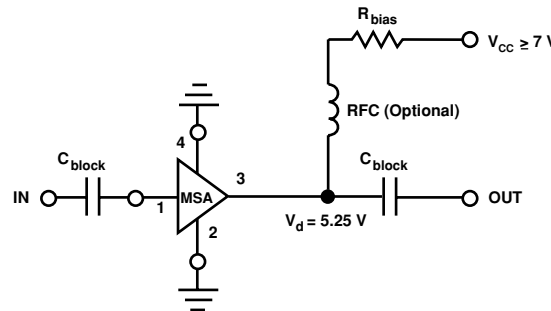
### 70 mil Package



### Features

- Cascadable 50  $\Omega$  Gain Block
- 3 dB Bandwidth:  
DC to 4.0 GHz
- 12.5 dBm Typical  $P_{1\text{ dB}}$  at  
1.0 GHz
- 8.5 dB Typical Gain at  
1.0 GHz
- Unconditionally Stable  
( $k > 1$ )
- Hermetic Gold-ceramic  
Microstrip Package

### Typical Biasing Configuration



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### MSA-0470 Absolute Maximum Ratings

| Parameter                          | Absolute Maximum <sup>[1]</sup> |
|------------------------------------|---------------------------------|
| Device Current                     | 100 mA                          |
| Power Dissipation <sup>[2,3]</sup> | 650 mW                          |
| RF Input Power                     | +13 dBm                         |
| Junction Temperature               | 200°C                           |
| Storage Temperature                | –65 to 200°C                    |

**Thermal Resistance<sup>[2,4]</sup>:**

$$\theta_{jc} = 115^{\circ}\text{C/W}$$

**Notes:**

1. Permanent damage may occur if any of these limits are exceeded.
2.  $T_{\text{CASE}} = 25^{\circ}\text{C}$ .
3. Derate at  $8.7 \text{ mW/}^{\circ}\text{C}$  for  $T_{\text{C}} > 125^{\circ}\text{C}$ .
4. The small spot size of this technique results in a higher, though more accurate determination of  $\theta_{jc}$  than do alternate methods.

### Electrical Specifications<sup>[1]</sup>, $T_{\text{A}} = 25^{\circ}\text{C}$

| Symbol                | Parameters and Test Conditions: $I_{\text{d}} = 50 \text{ mA}$ , $Z_{\text{o}} = 50 \Omega$ | Units                  | Min. | Typ.      | Max.      |
|-----------------------|---|------------------------|------|-----------|-----------|
| $G_{\text{P}}$        | Power Gain ( $ S_{21} ^2$ ) $f = 0.1 \text{ GHz}$   | dB                     | 7.5  | 8.5       | 9.5       |
| $\Delta G_{\text{P}}$ | Gain Flatness $f = 0.1 \text{ to } 2.5 \text{ GHz}$   | dB                     |      | $\pm 0.6$ | $\pm 1.0$ |
| $f_{3 \text{ dB}}$    | 3 dB Bandwidth  | GHz                    |      | 4.0       |           |
| VSWR                  | Input VSWR $f = 0.1 \text{ to } 2.5 \text{ GHz}$  |                        |      | 1.7:1     |           |
|                       | Output VSWR $f = 0.1 \text{ to } 2.5 \text{ GHz}$   |                        |      | 2.0:1     |           |
| NF                    | 50 $\Omega$ Noise Figure $f = 1.0 \text{ GHz}$  | dB                     |      | 6.5       |           |
| $P_{1 \text{ dB}}$    | Output Power at 1 dB Gain Compression $f = 1.0 \text{ GHz}$                                 | dBm                    |      | 12.5      |           |
| $\text{IP}_3$         | Third Order Intercept Point $f = 1.0 \text{ GHz}$   | dBm                    |      | 25.5      |           |
| $t_{\text{D}}$        | Group Delay $f = 1.0 \text{ GHz}$   | psec                   |      | 125       |           |
| $V_{\text{d}}$        | Device Voltage  | V                      | 4.75 | 5.25      | 5.75      |
| $\text{dV/dT}$        | Device Voltage Temperature Coefficient  | mV/ $^{\circ}\text{C}$ |      | –8.0      |           |

**Note:**

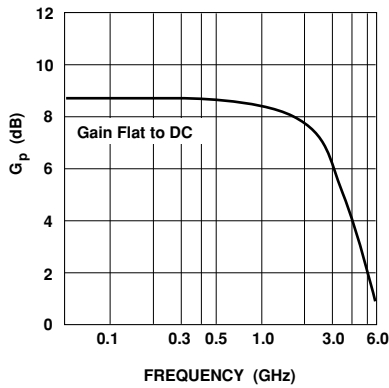
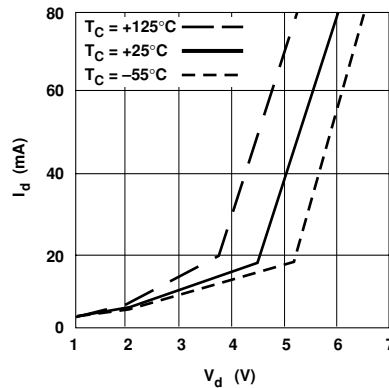
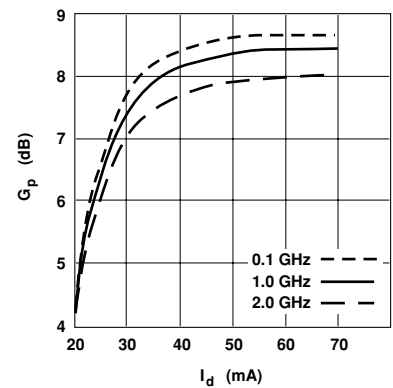
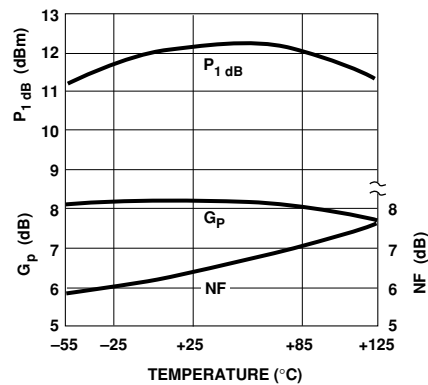
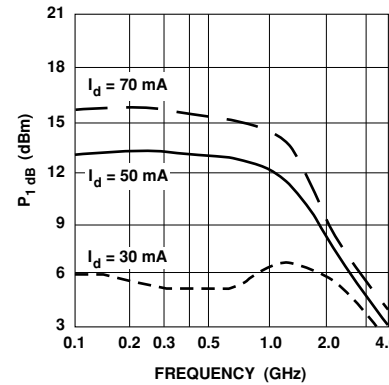
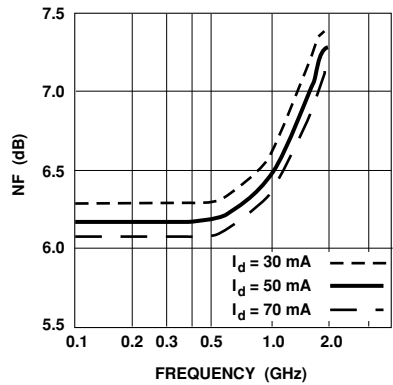
1. The recommended operating current range for this device is 30 to 70 mA. Typical performance as a function of current is on the following page.

**MSA-0470 Typical Scattering Parameters ( $Z_0 = 50 \Omega$ ,  $T_A = 25^\circ\text{C}$ ,  $I_d = 50 \text{ mA}$ )**

| Freq.<br>GHz | $S_{11}$ |      | $S_{21}$ |      |     | $S_{12}$ |      |     | $S_{22}$ |      |
|--------------|----------|------|----------|------|-----|----------|------|-----|----------|------|
|              | Mag      | Ang  | dB       | Mag  | Ang | dB       | Mag  | Ang | Mag      | Ang  |
| 0.1          | .18      | 179  | 8.5      | 2.67 | 176 | -16.4    | .151 | 1   | .10      | -14  |
| 0.2          | .18      | 179  | 8.5      | 2.67 | 172 | -16.4    | .151 | 2   | .10      | -30  |
| 0.4          | .18      | 179  | 8.5      | 2.67 | 163 | -16.4    | .152 | 3   | .13      | -50  |
| 0.6          | .17      | -179 | 8.5      | 2.65 | 155 | -16.2    | .155 | 5   | .16      | -67  |
| 0.8          | .16      | -176 | 8.4      | 2.64 | 147 | -16.1    | .158 | 8   | .19      | -79  |
| 1.0          | .16      | -174 | 8.3      | 2.61 | 138 | -15.9    | .161 | 6   | .22      | -90  |
| 1.5          | .16      | -166 | 8.2      | 2.56 | 117 | -15.5    | .169 | 9   | .29      | -111 |
| 2.0          | .21      | -163 | 7.8      | 2.46 | 97  | -14.6    | .186 | 9   | .33      | -131 |
| 2.5          | .26      | -162 | 7.3      | 2.33 | 83  | -13.8    | .204 | 12  | .36      | -142 |
| 3.0          | .32      | -170 | 6.5      | 2.12 | 65  | -13.5    | .212 | 10  | .40      | -156 |
| 3.5          | .37      | -177 | 5.7      | 1.93 | 38  | -13.2    | .220 | 7   | .40      | -164 |
| 4.0          | .40      | 175  | 4.7      | 1.73 | 33  | -12.6    | .234 | 3   | .40      | -170 |
| 4.5          | .41      | 166  | 3.9      | 1.57 | 20  | -12.4    | .239 | -1  | .39      | -173 |
| 5.0          | .42      | 155  | 3.1      | 1.44 | 7   | -11.9    | .255 | -6  | .37      | -176 |

**Typical Performance,  $T_A = 25^\circ\text{C}$** 

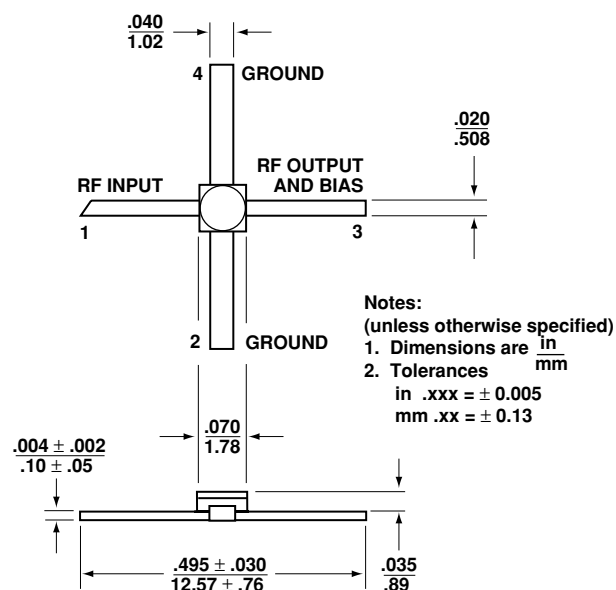
(unless otherwise noted)


**Figure 1. Typical Power Gain vs. Frequency,  $T_A = 25^\circ\text{C}$ ,  $I_d = 50 \text{ mA}$ .**

**Figure 2. Device Current vs. Voltage.**

**Figure 3. Power Gain vs. Current.**

**Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature,  $f = 1.0 \text{ GHz}$ ,  $I_d = 50 \text{ mA}$ .**

**Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.**

**Figure 6. Noise Figure vs. Frequency.**

## Ordering Information

| Part Numbers | No. of Devices | Comments |
|--------------|----------------|----------|
| MSA-0470     | 10             | Bulk     |

## 70 mil Package Dimensions



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